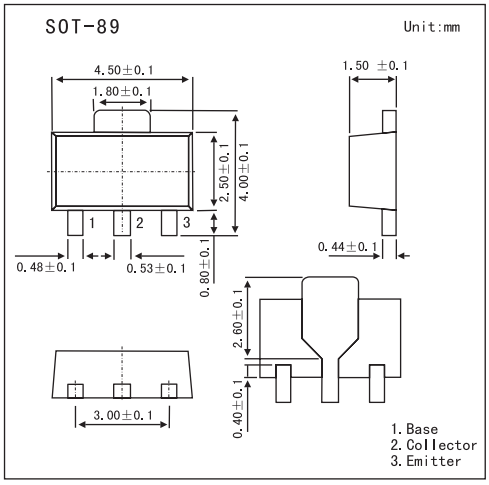
Silicon PNP Epitaxial

2SA1944



■ Features

- High voltage V_{CEO}=-50V
- Low collector to emitter saturation voltage
  $V_{CE(sat)}$=-0.2v typ (@I_C=-500mA, I_B=-10mA)
- High h_{FE}: h_{FE}=400 to 800
- Small package for mounting

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-50	V
Emitter-base voltage	V_{EBO}	-6	V
Collector-emitter voltage	V_{CEO}	-50	V
Peak collector current	I_{CM}	-2	A
Collector current	I_C	-1	A
Collector dissipation (Ta=25℃)	P_C	500	mW
Jumction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Colllector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-10μA,I_E=0	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-10μA,I_C=0	-6			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA,R_{BE}=∞	-50			V
Collector cutoff current	I_{CBO}	V_{CB}=-40V,I_E=0			-0.1	μA
Emitter cutoff current	I_{EBO}	V_{EB}=-2V,I_C=0			-0.1	μA
DC current gain	h_{FE}	V_{CE}=-6V,I_C=-100mA	400		800	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500mA,I_B=-10mA		-0.2	-0.5	V
Gain bandwidth product	f_T	V_{CE}=-10V,I_E=-10mA		90		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0,f=1MHz		30		pF

■ Marking

Marking	XG